SUPER-SEMI

Super Junction Insulated Gate Bipolar Transistor

650V Trench and Super Junction IGBT
SI*50N65G2P2G

Rev. 0.9
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www.supersemi.com.cn

SIW50N65G2P2G

SJBT® Discrete

650V Trench and Super Junction IGBT

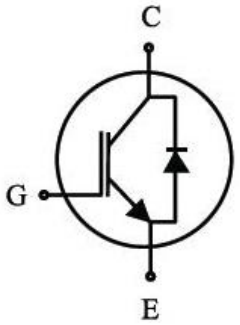
General Description

Super-Semi Trench and Super Junction IGBTs, designed according to the super junction (SJ) technology. The SJ-IGBT series provides low switching losses, high energy efficiency and high avalanche ruggedness for motor control, solar application and welding machine, etc.

V_{CE}	650	V
I_C	50	A
$V_{CE(sat)}$, I_C=50A	1.62	V

Features

- High breakdown voltage to 600V for improved reliability
- Super junction Technology offering :
  - High speed switching
  - High ruggedness, temperature stable
  - Low $V_{CE(sat)}$
  - Easy parallel switching capability due to positive temperature coefficient in $V_{CE(sat)}$
- Enhanced avalanche capability



SIW50N65G2P2G

TO-247

Applications

- Uninterruptible Power Supply(UPS)
- Power Factor Correction(PFC)
- Welding Converters
- Inverter
- Converter with high switching frequency

Absolute Maximum Ratings (Tj= 25 ℃ unless otherwise specified)

Symbol	Parameter	SIW50N65G2P2G	Unit
V_{CE}	Collector-Emitter Breakdown Voltage	650	V
I_C	DC collector current* -Continuous (T_C = 25℃) -Continuous (T_C = 100℃)	 100 50	A
I_F	Diode Forward current* -Continuous (T_C = 25℃) -Continuous (T_C = 100℃)	 100 50	A
V_{GE}	Continuous Gate-Emitter Voltage	±20	V
	Transient Gate-Emitter Voltage	±30	V
I_{CM}	Pulsed Collector Current, V_{GE} =15V, tp limited by Tjmax	150	A
T_J	Operating junction temperature	-40 to +175	℃
T_{STG}	Storage Temperature Range	-55 to +150	℃
P_D	Power Dissipation， T_C = 25℃	130	W
M	Mounting torque （TO-220,TO-247) M3 and M3.5 screws	60	Ncm
	Mounting torque （TO-220F) M2.5 screws	50	
	Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s	260	℃

* Current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	Typ. Value	Unit
IGBT	$R_{\theta JC}$ Thermal Resistance, Junction-to-Case	1.15	℃/W
	$R_{\theta JA}$ Thermal Resistance, Junction-to-Ambient	40	℃/W
FRD	$R_{\theta JC}$ Thermal Resistance, Junction-to-Case	1.04	℃/W
	$R_{\theta JA}$ Thermal Resistance, Junction-to-Ambient	40	℃/W

Electrical Characteristics (Tj= 25 ℃ unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	V_{GE} = 0V, I_C = 250μA	650	-	-	V
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE}, I_C = 250μA	4.0	5.0	6.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{GE} = 15V, I_C = 50A -T_J = 25℃ -T_J = 150℃	 - -	 1.62 1.92	 2.0 -	 V V
I_{CES}	Zero Gate Voltage Collector Current	V_{CE} = 650V, V_{GE} = 0V -T_J = 25℃ -T_J = 150℃	 - -	 0.1 -	 20 1000	 μA μA
I_{GES}	Gate-Emitter Leakage Current	V_{CE} = 0V, V_{GE} = ±20V	-	-	100	nA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic Characteristics						
Cies	Input Capacitance	V_{CE} = 25V, V_{GE} = 0V, f = 1.0MHz	-	1700	-	pF
Coes	Output Capacitance		-	85	-	pF
Cres	Reverse Transfer Capacitance		-	25	-	pF
Q_G	Gate Charge	V_{CC} = 400V, I_C = 50A, V_{GE} = 15V	-	66.8	-	nC

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Switching Characteristics, Inductive Load, Tj=25℃						
td(on)	Turn-On Delay Time	Vcc = 400V, I_C = 50A V_{GE} = 0V/15V Rg = 10Ω	-	28	-	ns
tr	Turn-On Rise Time		-	45	-	ns
td(off)	Turn-Off Delay Time		-	87	-	ns
tf	Turn-Off Fall Time		-	116	-	ns
Eon	Turn-on Energy		-	1.01	-	mJ
Eoff	Turn-off Energy		-	0.67	-	mJ

Electrical Characteristics (Tj= 25 ℃ unless otherwise specified)

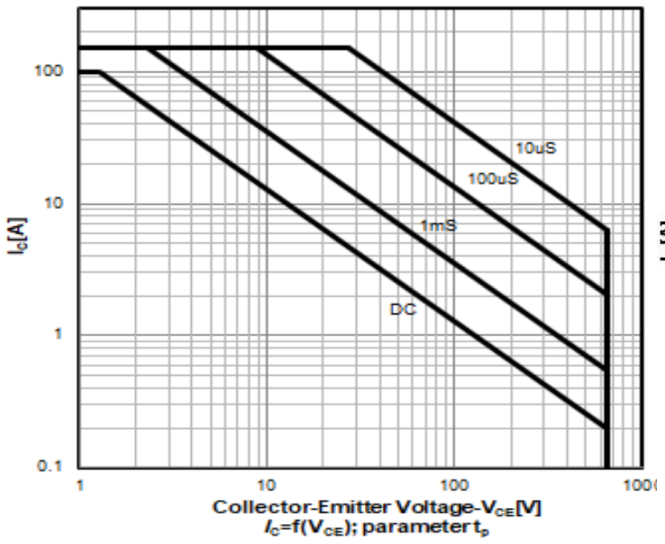
Switching Characteristics, Inductive Load, Tj=150℃						
td(on)	Turn-On Delay Time	Vcc = 400V, I_C = 50A V_{GE} = 0V/15V Rg = 10Ω	-	28	-	ns
tr	Turn-On Rise Time		-	44	-	ns
td(off)	Turn-Off Delay Time		-	89	-	ns
tf	Turn-Off Fall Time		-	143	-	ns
Eon	Turn-on Energy		-	1.14	-	mJ
Eoff	Turn-off Energy		-	1.03	-	mJ

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Diode Characteristics and Maximum Ratings, Tj=25℃						
V_{FM}	Diode Forward Voltage	I_F = 25A	-	1.61	1.9	V
Trr	Reverse Recovery Time	VR = 400V, I_F = 25A dI_F/dt =1000A/μs	-	22	-	ns
Irr	Reverse Recovery Current		-	35	-	A
Qrr	Reverse Recovery Charge		-	0.33	-	μC
Trr	Reverse Recovery Time	VR = 400V, I_F = 50A dI_F/dt =500A/μs	-	84	-	ns
Irr	Reverse Recovery Current		-	23	-	A
Qrr	Reverse Recovery Charge		-	1.07	-	μC

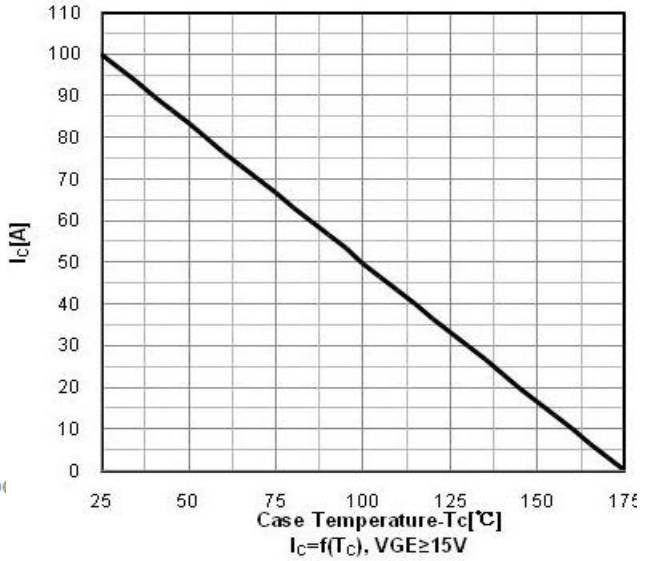
Diode Characteristics and Maximum Ratings, Tj=150℃						
V_{FM}	Diode Forward Voltage	I_F = 25A	-	1.32	1.6	V
Trr	Reverse Recovery Time	VR = 400V, I_F = 25A dI_F/dt =1000A/μs	-	40	-	ns
Irr	Reverse Recovery Current		-	40	-	A
Qrr	Reverse Recovery Charge		-	0.88	-	μC
Trr	Reverse Recovery Time	VR = 400V, I_F = 50A dI_F/dt =500A/μs	-	166	-	ns
Irr	Reverse Recovery Current		-	32	-	A
Qrr	Reverse Recovery Charge		-	2.75	-	μC

Typical Performance Characteristics

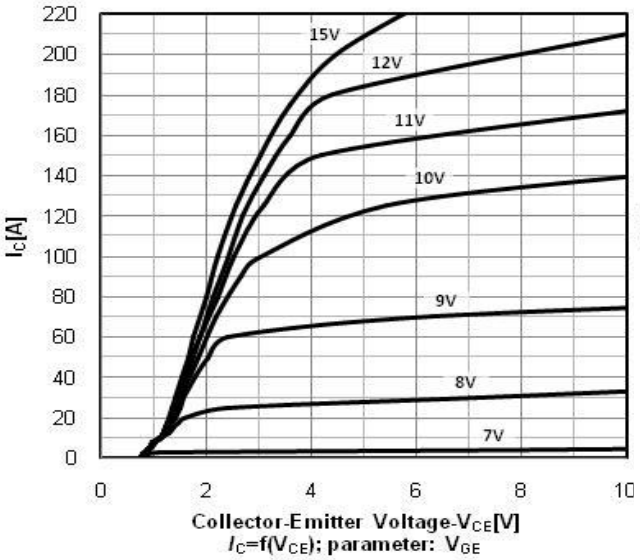
Safe operating area Ta=25 ℃
Non-Full PAK



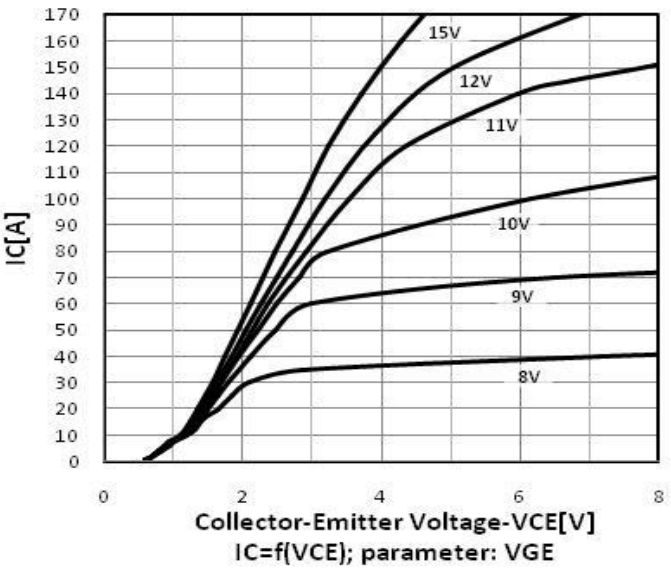
Collector current as a function of
Case temperature



Typ. Output characteristics
Tj=25 ℃

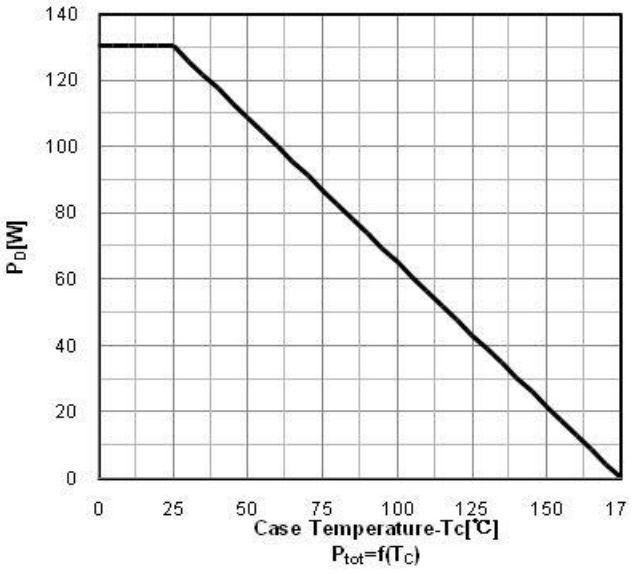


Typ. Output characteristics
Tj=150 ℃

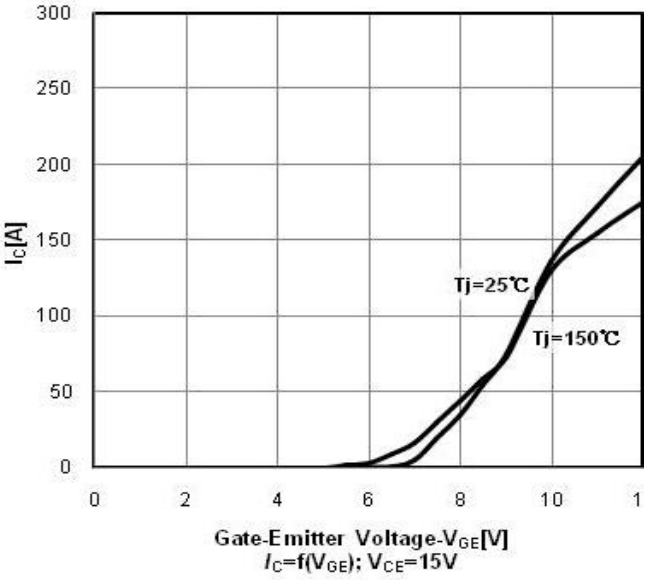


Typical Performance Characteristics

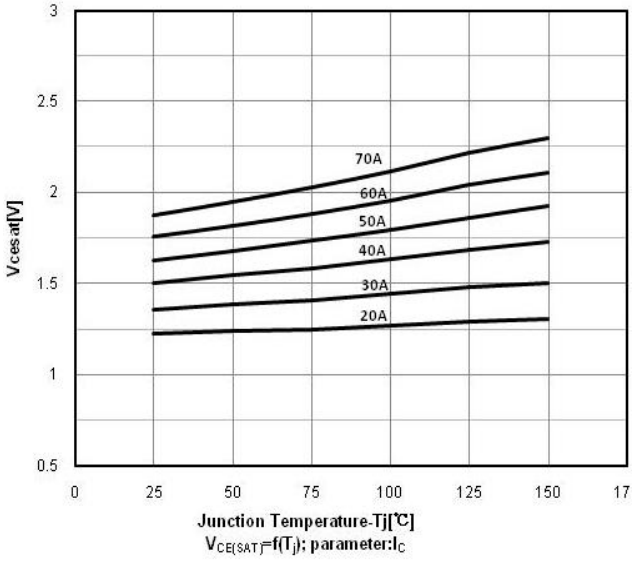
Power dissipation



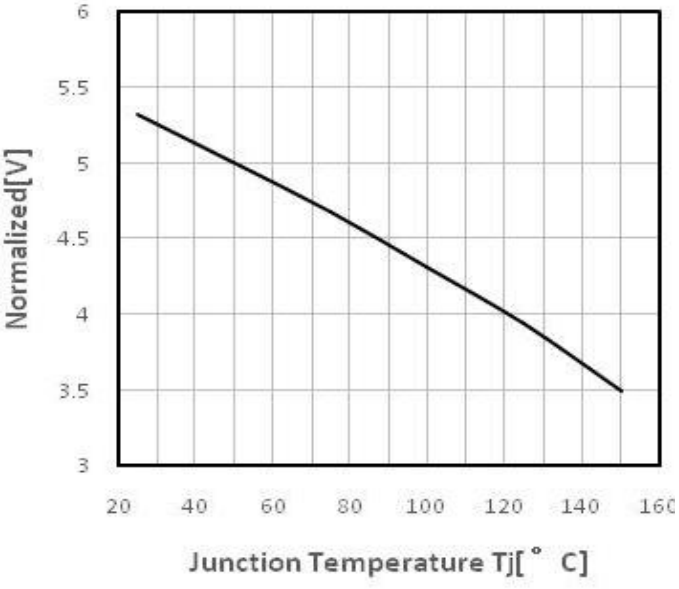
Typ. Transfer characteristics



Typ. Collector-emitter saturation voltage as a function of junction temperature (V_{GE}=15V)

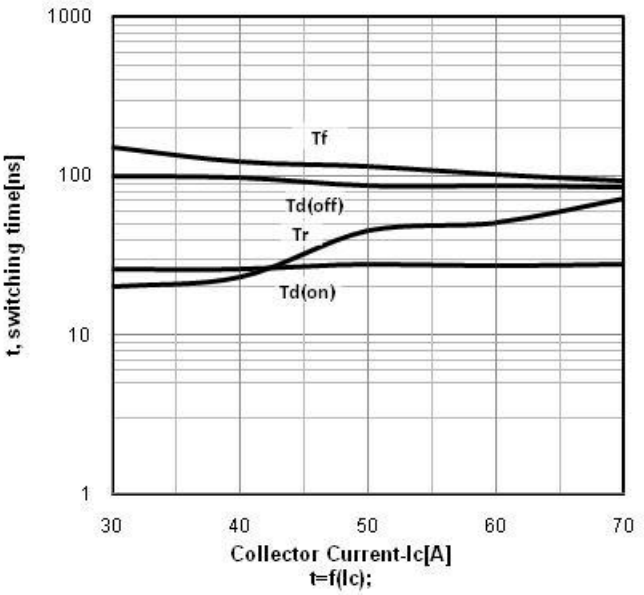


Normalized $V_{GE(th)}$ vs. temperature

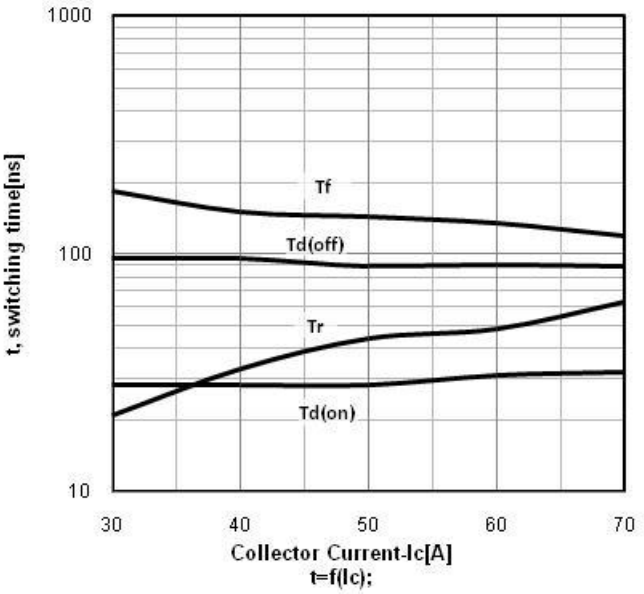


Typical Performance Characteristics

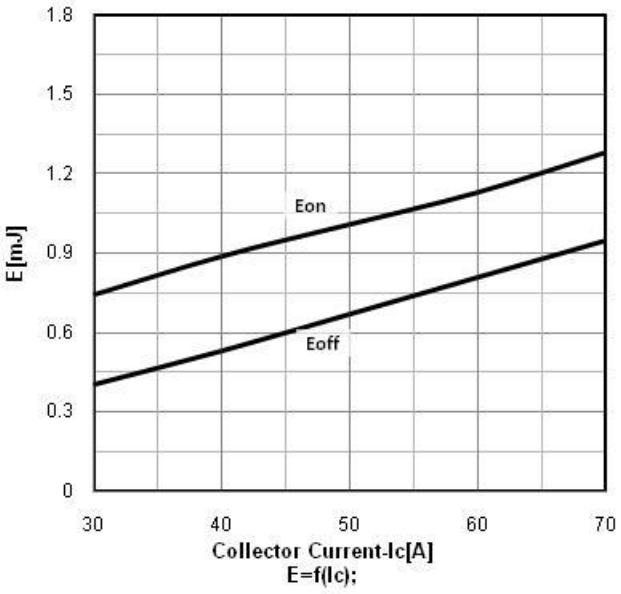
Switching times vs collector current
Tj=25 ℃



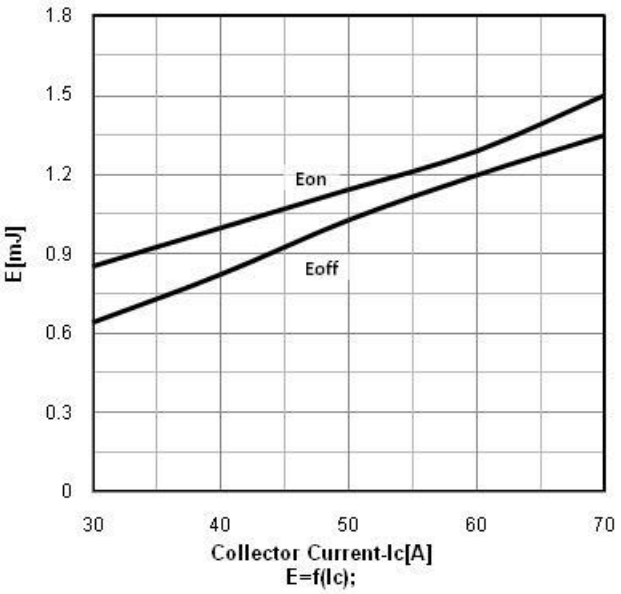
Switching times vs collector current
Tj=150 ℃



Switching energy losses vs collector current
Tj=25 ℃

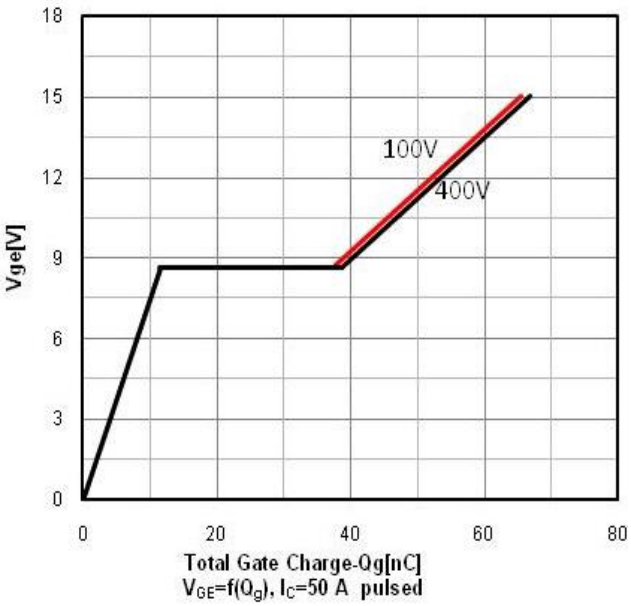


Switching energy losses vs collector current
Tj=150 ℃

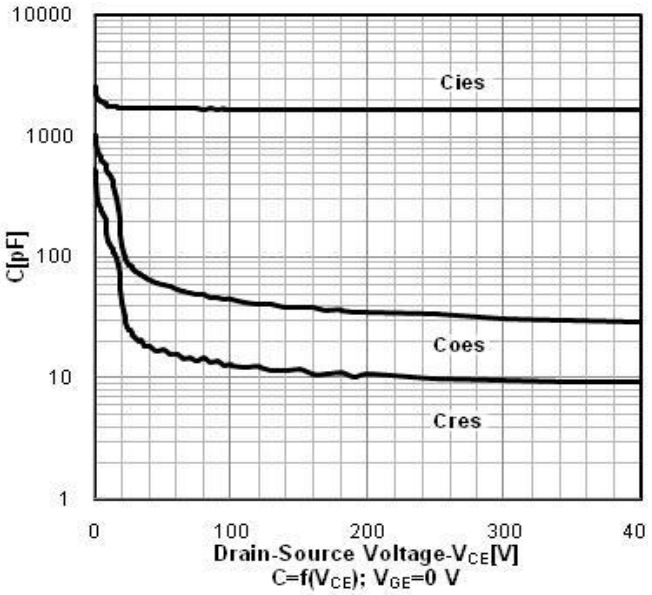


Typical Performance Characteristics

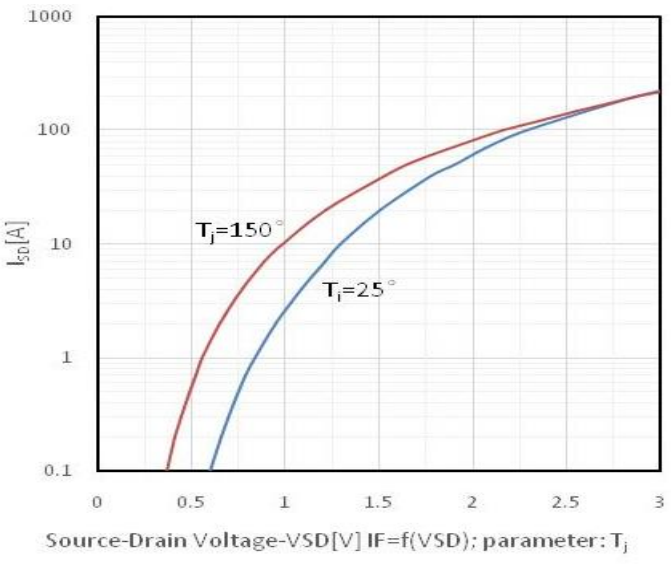
Gate charge characteristics



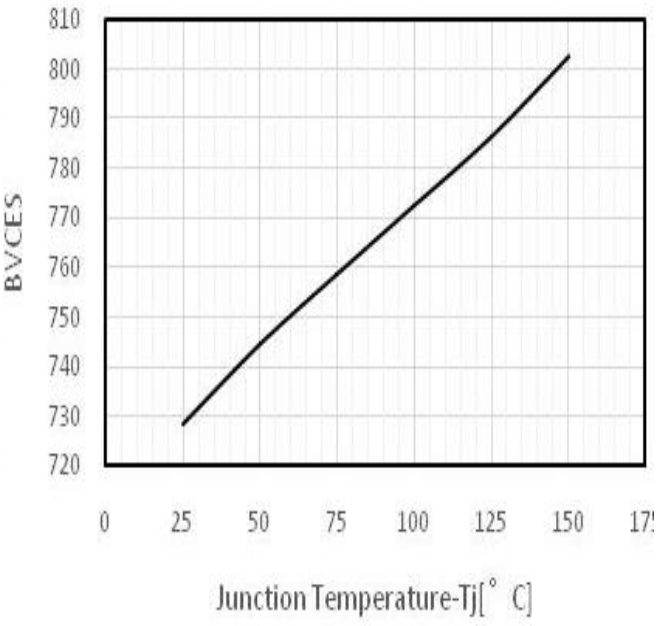
Capacitance characteristics



Diode Forward Voltage

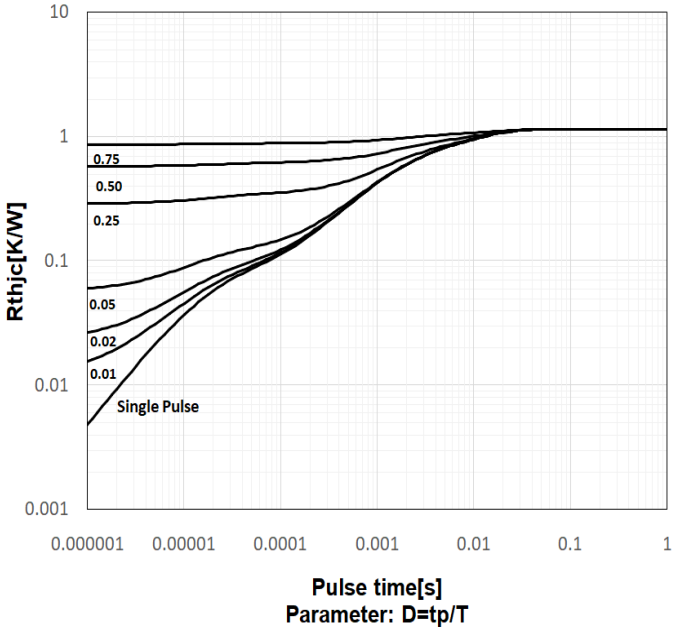


Collector-emitter breakdown voltage vs. temperature

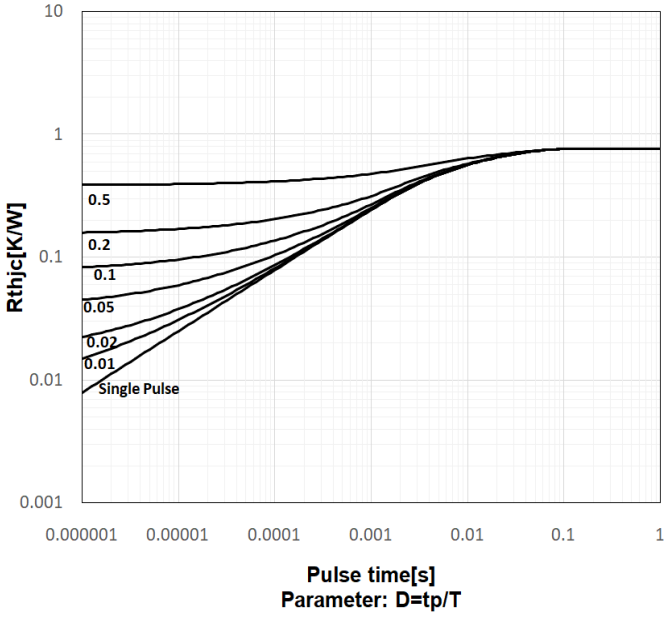


Typical Performance Characteristics

Max. transient thermal impedance parameter: D=tp/T; IGBT

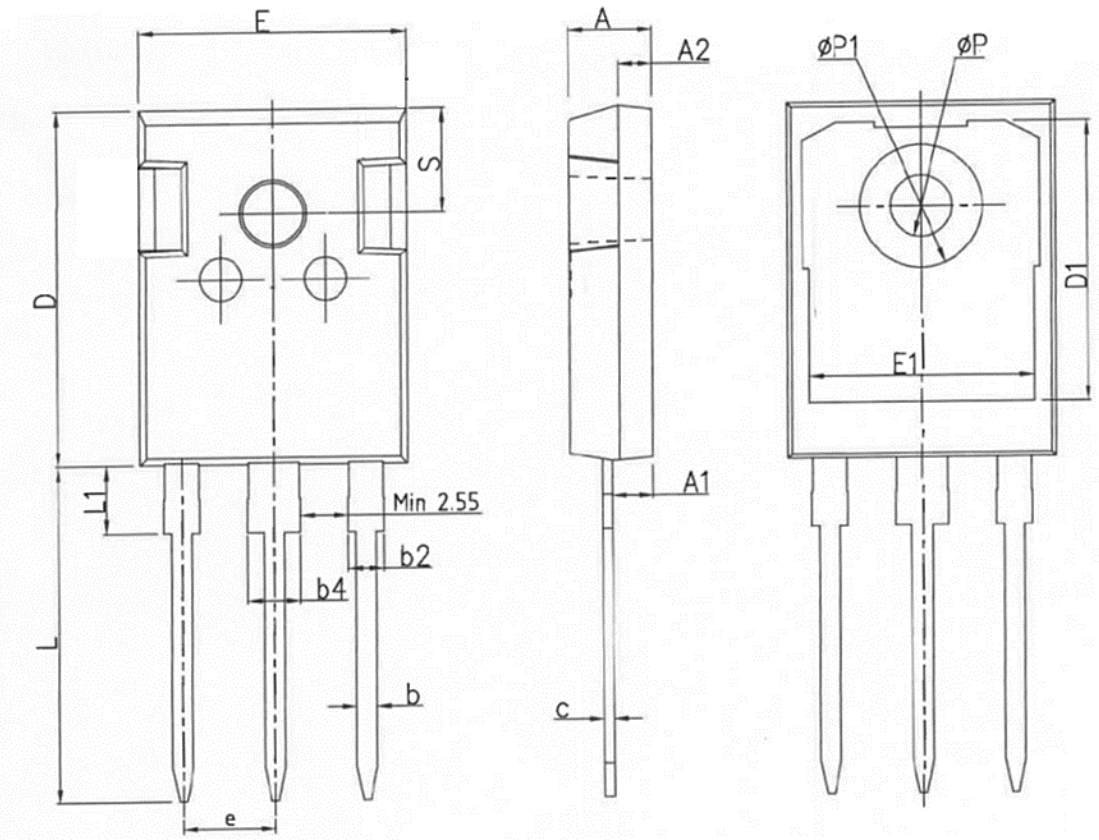


Max. transient thermal impedance parameter: D=tp/T; Diode



Package Outline

TO-247



COMMON DIMENSIONS

SYMBOL	UNIT(mm)		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.20	2.40	2.60
A2	1.85	2.00	2.15
b	1.10	1.20	1.35
b2	1.91	2.04	2.21
b4	2.91	3.04	3.21
c	0.50	0.60	0.75
D	20.70	21.00	21.30
D1	16.20	16.55	16.90
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
e	5.44BSC		
L	19.60	19.95	20.30
L1	-	-	4.30
ΦP	3.40	3.60	3.80
ΦP1	-	-	7.50
S	6.15BSC		

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